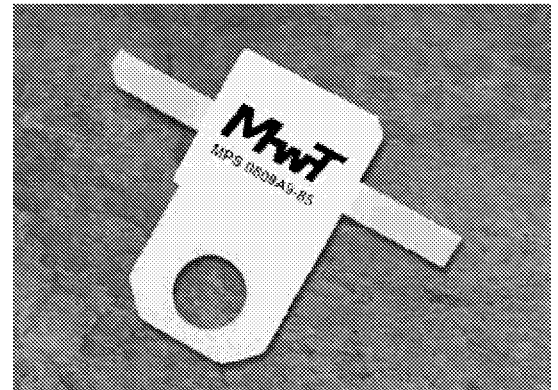


Features

- Very Low Noise 1.1 dB Typical
- High +36 dBm Typical IP3
- 16 dB Typical Gain
- 6.0 Volt Bias
- 26% High Power Added Efficiency



Description

The MPS-0808A9-85 is a low noise, high dynamic range amplifier designed for ultra linear receiver applications in the 806 to 849 MHz frequency range. The circuit is matched to 50 Ω and employs a single stage GaAs FET with internal matching to provide exceptional noise figure, 1.1 dB combined with extremely high IP3, +36 dBm. Typical applications are cellular base station receivers, Tower mounted LNA's, smart antenna systems and receiver multi-couplers.

Electrical Specifications at 25°C, V_{dd} = 6.0 V, Z_o = 50 Ω

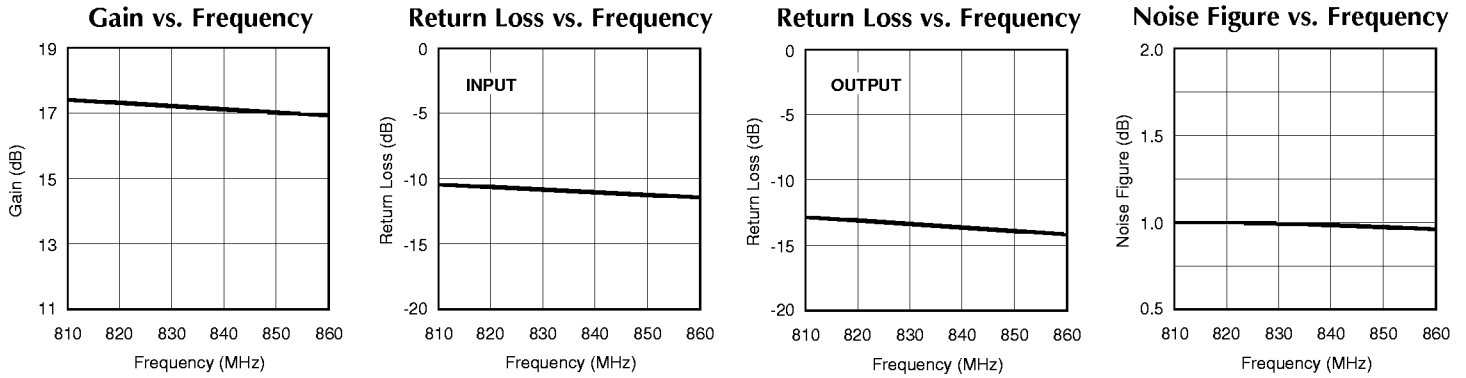
Symbol	Parameter	Minimum	Typical	Maximum	Unit
Freq	Frequency Range	806		849	MHz
SSG	Small Signal Gain	14	16		dB
P1dB	Pout at 1 dB Compression		+21.5		dBm
IP3	Third-order Intercept ¹	+33.0	+36.0		dBm
NF	Noise Figure		1.1	1.5	dB
VSWR	Input/Output VSWR		2.0:1	2.5:1	
Δ GOF	Gain Variation over Frequency		± 0.2	± 0.5	dB
Δ GOT	Gain Variation over Temperature		-0.15		dB/°C
I _{dd}	DC Current		180	250	mA
PAE	Power Added Efficiency		26		%

¹ Two tone test at +5 dBm per tone output.

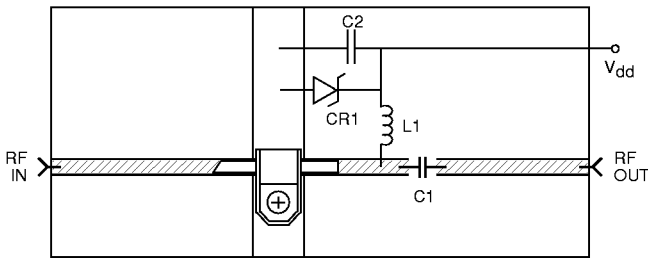
Absolute Maximum Ratings

Maximum Bias Voltage	7.0 V
Maximum Continuous RF Input Power	240 mW
Maximum Peak Input Power	360 mW
Maximum Case Operating Temperature	+85°C
Maximum Storage Temperature	-65°C to +150°C

Typical Performance at +25°C



Application Circuit

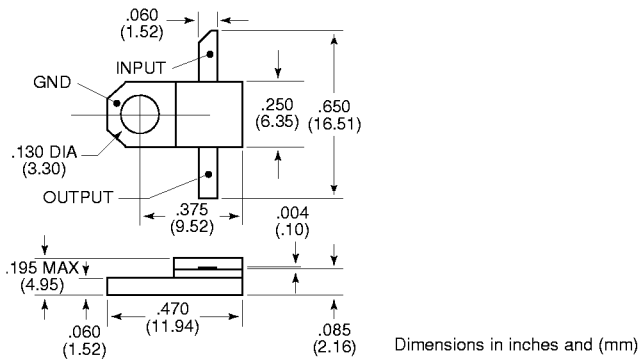


- | | | |
|-----|--------|-----------------------|
| C1 | 100 pF | Chip Capacitor |
| C2 | .22 μF | Capacitor |
| L1 | 160 nH | Printed or Wound Coil |
| CR1 | 7.0 V | Zener Diode |
| | | 50 Ω Microstrip Line |

Board material FR-4 or equivalent.

Outline Diagram

Half Flange Package (-85)



Ordering Information

Part Number	Package
MPS-0808A9-85	Half Flange Package
MPS-0808A9-85EV	Half Flange Package on Evaluation Board